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(54) Title: STRESS CONTROL METHOD FOR PHYSICAL VAPOR DEPOSITION OF ALUMINUM

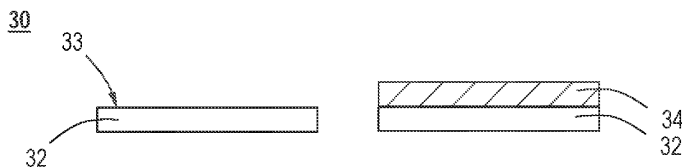


FIG. 1B

(57) Abstract: Provided are methods of reducing the stress of a semiconductor wafer. The method includes exposing depositing an aluminum layer on a top surface of a substrate; and cooling the substrate to a temperature of less than or equal to 20 °C, or less than or equal to 10 °C, or less than or equal to 0 °C, or less than or equal to -20 °C. In some embodiments, the method is conducted within a processing tool, e.g., a cluster tool.

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